

ESD5306D
**6-Lines, Uni-directional, Ultra-low Capacitance
Transient Voltage Suppressors**
<http://www.sh-willsemi.com>
Descriptions

The ESD5306D is an ultra-low capacitance TVS (Transient Voltage Suppressor) array designed to protect high speed data interfaces. It has been specifically designed to protect sensitive electronic components which are connected to data and transmission lines from over-stress caused by ESD (Electrostatic Discharge).

The ESD5306D incorporates six lines of ultra- low capacitance TVS diode.

The ESD5306D may be used to provide ESD protection up to $\pm 20\text{kV}$ (contact discharge) according to IEC61000-4-2, and withstand peak pulse current up to 5A (8/20 μs) according to IEC61000-4-5.

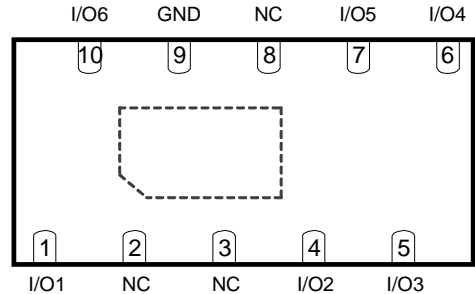
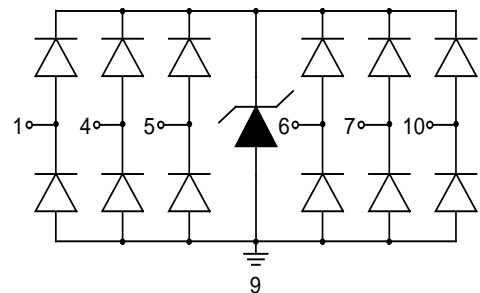
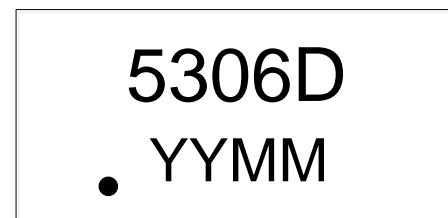
The ESD5306D is available in DFN4120-10L package. Standard products are Pb-free and Halogen-free.

Features

- Stand-off voltage: 5V Max
- Transient protection for each line according to IEC61000-4-2 (ESD): $\pm 20\text{kV}$ (contact discharge)
IEC61000-4-5 (surge): 4A (8/20 μs)
- Ultra-low capacitance: $C_J = 0.4\text{pF}$ typ.
- Ultra-low leakage current: $I_R < 1\text{nA}$ typ.
- Low clamping voltage: $V_{CL} = 19\text{V}$ @ $I_{PP} = 16\text{A}$ (TLP)
- Solid-state silicon technology

Applications

- USB 2.0 and USB 3.0
- HDMI 1.3 and HDMI 1.4
- SATA and eSATA
- DVI
- IEEE 1394
- PCI Express
- Notebooks


DFN4120-10L (Top View)

Circuit diagram


5306D = Device code

YYMM = Data code

Marking (Top View)
Order information

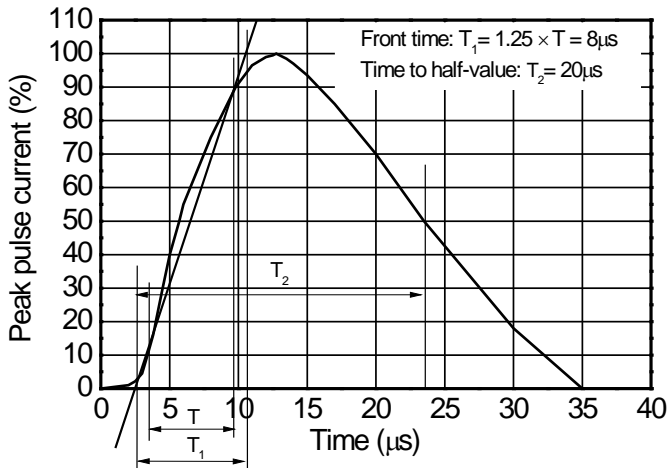
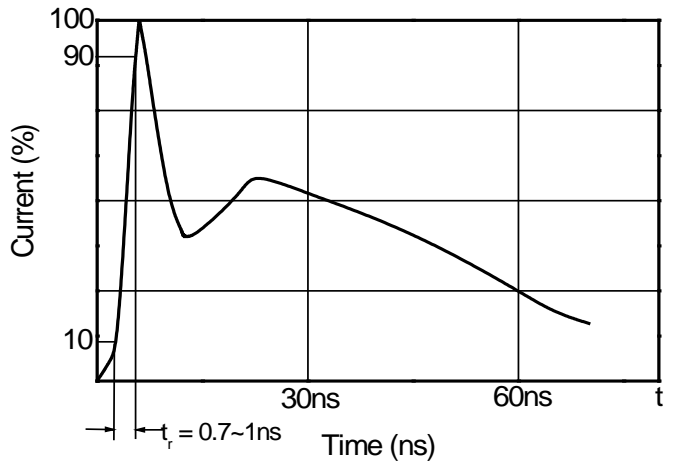
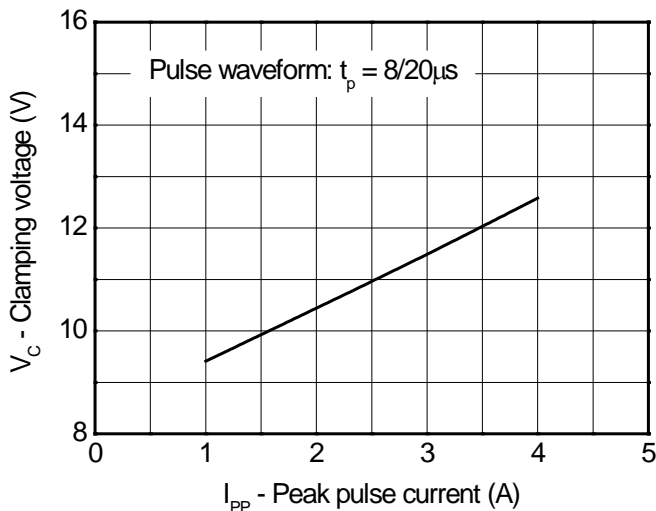
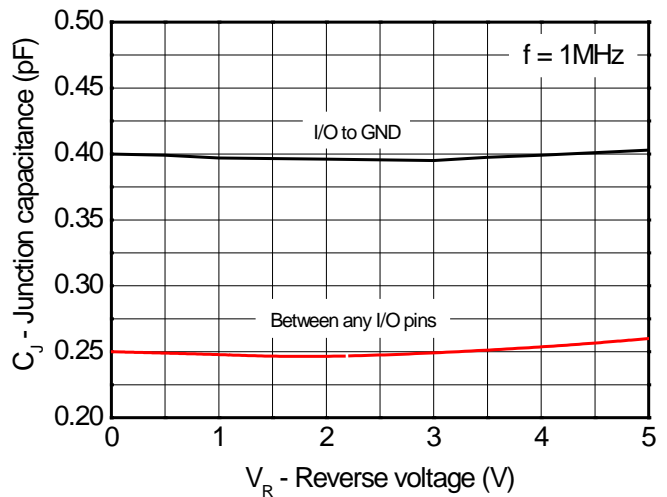
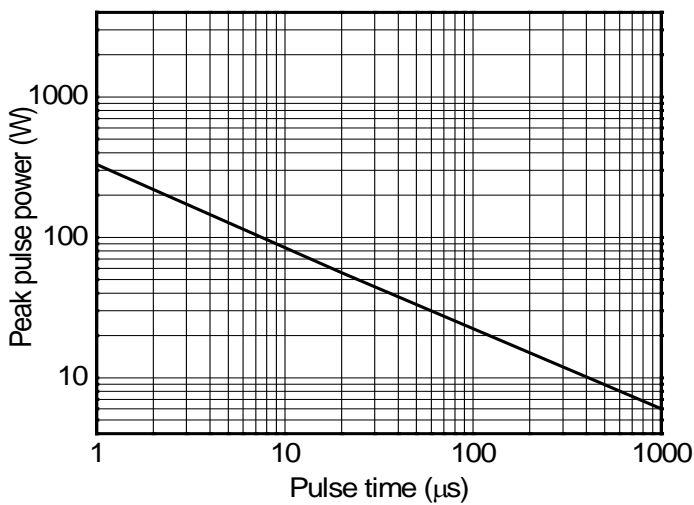
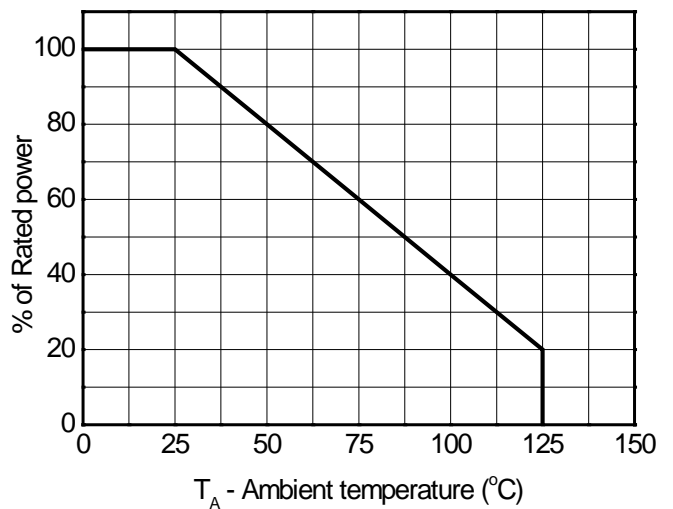
Device	Package	Shipping
ESD5306D-10/TR	DFN4120-10L	6000/Tape&Reel

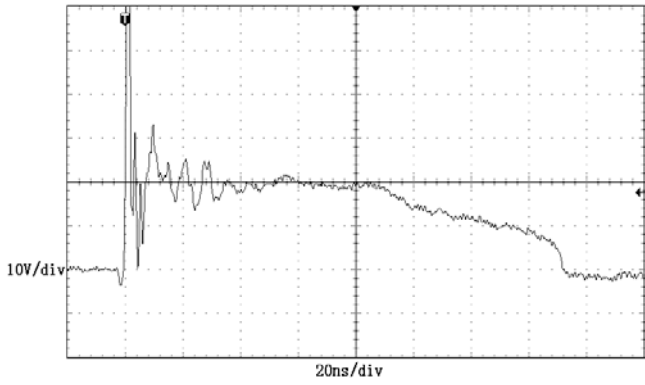
Absolute maximum ratings

Parameter	Symbol	Rating	Unit
Operation junction temperature	T_J	125	$^{\circ}\text{C}$
Lead temperature	T_L	260	$^{\circ}\text{C}$
Storage temperature	T_{STG}	-55~150	$^{\circ}\text{C}$
ESD according to IEC61000-4-2 air discharge	V_{ESD}	± 20	kV
ESD according to IEC61000-4-2 contact discharge		± 20	
Peak pulse power ($t_p = 8/20\mu\text{s}$)	P_{pk}	56	W
Peak pulse current ($t_p = 8/20\mu\text{s}$)	I_{PP}	4	A

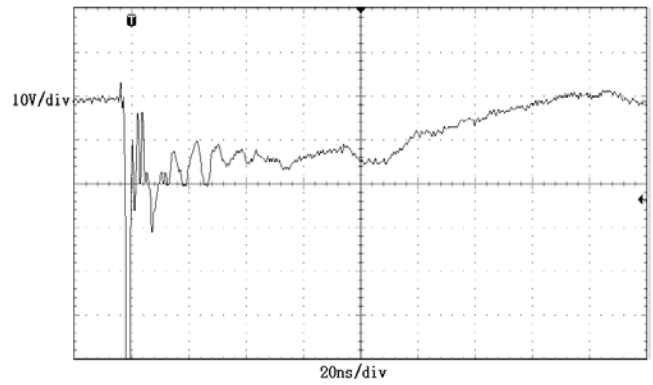
Electrical characteristics ($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse maximum working voltage	V_{RWM}				5.0	V
Reverse leakage current	I_R	$V_{\text{RWM}} = 5\text{V}$		<1	100	nA
Reverse breakdown voltage	V_{BR}	$I_T = 1\text{mA}$	7.0	8.0	9.0	V
Forward voltage	V_F	$I_T = 10\text{mA}$	0.6	0.9	1.2	V
Clamping voltage	V_{CL}	$I_{\text{PP}} = 16\text{A}$, $t_p = 100\text{ns}$		19.0		V
Dynamic resistance	R_{DYN}			0.65		Ω
Clamping voltage	V_{CL}	$I_{\text{PP}} = 1\text{A}$, $t_p = 8/20\mu\text{s}$			11	V
		$I_{\text{PP}} = 4\text{A}$, $t_p = 8/20\mu\text{s}$			14	V
Junction capacitance	C_J	$V_R = 0\text{V}$, $f = 1\text{MHz}$ Any I/O pin to GND		0.40	0.65	pF
		$V_R = 0\text{V}$, $f = 1\text{MHz}$ Between any I/O pin		0.25	0.40	pF

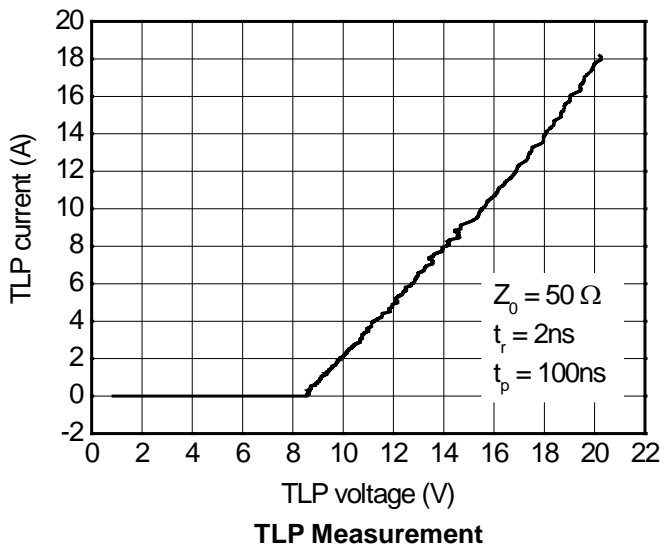
Typical characteristics ($T_A=25^\circ\text{C}$, unless otherwise noted)

8/20 μs waveform per IEC61000-4-5

Contact discharge current waveform per IEC61000-4-2

Clamping voltage vs. Peak pulse current

Capacitance vs. Reverse voltage

Non-repetitive peak pulse power vs. Pulse time

Power derating vs. Ambient temperature

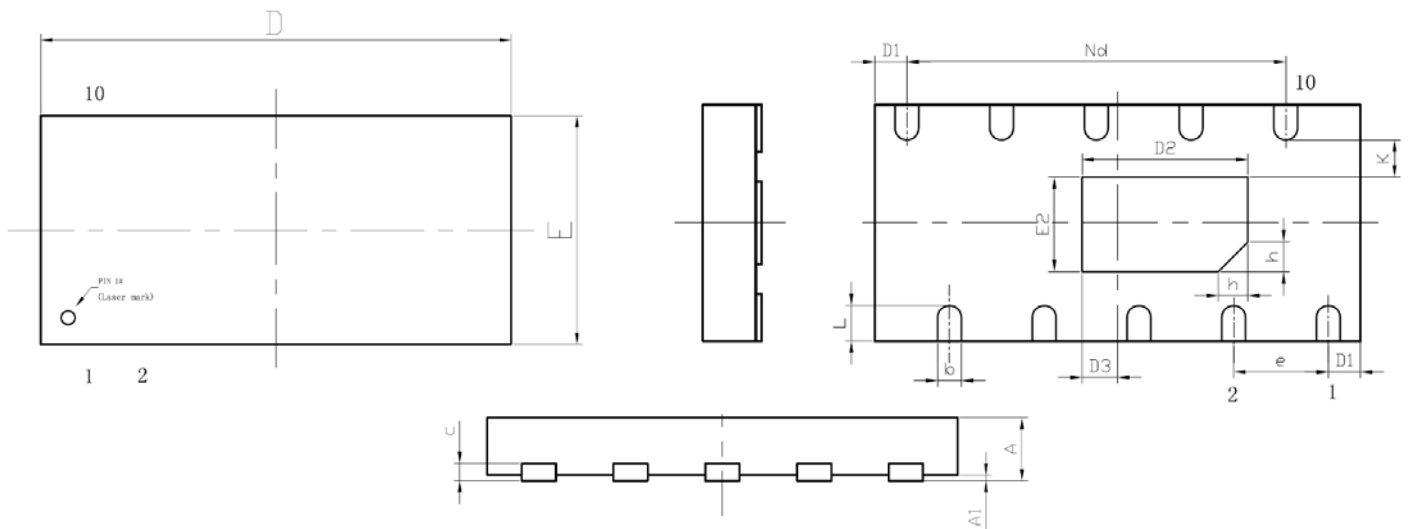


ESD clamping
 (+8kV contact discharge per IEC61000-4-2)



ESD clamping
 (-8kV contact discharge per IEC61000-4-2)



Package outline dimensions
DFN4120-10L


Symbol	Dimensions in millimeter		
	Min.	Nom.	Max.
A	0.45	0.50	0.55
A1	—	0.02	0.05
b	0.15	0.20	0.25
c	0.10	0.15	0.20
D	4.00	4.10	4.20
D1	0.20	0.25	0.30
D2	1.30	1.40	1.50
D3	0.25	0.30	0.35
e	0.80BSC		
Nd	3.20BSC		
E	1.90	2.00	2.10
E2	0.70	0.80	0.90
K	0.20	—	—
L	0.25	0.30	0.35
h	0.15	0.20	0.25
L/F Carrier Size (Mil)	67*43		